



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
100V	$8.8 \text{m}\Omega$ @ $V_{GS} = 10V$	68.8A
	11.3mΩ @ V _{GS} = 6.0V	60.7A
	15mΩ @ V _{GS} = 4.5V	52.7A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting



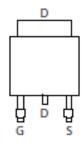
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

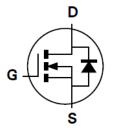
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 [®]3
- Weight: 0.33 grams (Approximate)







Pin Out Top View



Equivalent Circuit

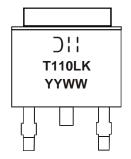
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H010LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Dil = Manufacturer's Marking
T110LK = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	100	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current,V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	I _D	68.8 55	А
Continuous Drain Current,V _{GS} = 6V	$T_C = +25$ °C $T_C = +70$ °C	I _D	60.7 48.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle=1%)	I _{DM}	250	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	52	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle =1%)	I _{SM}	250	Α	
Avalanche Current, L=3mH		I _{AS}	10	Α
Avalanche Energy, L=3mH		E _{AS}	150	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	3	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	42	°C/W
Total Power Dissipation (Note 6)	P _D	62.5	W
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	2	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.2	_	2.8	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	6.5	8.8		$V_{GS} = 10V, I_D = 13A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.8	11.3	mΩ	$V_{GS} = 6V, I_D = 13A$	
		_	12.5	15		$V_{GS} = 4.5V, I_D = 13A$	
Diode Forward Voltage	V_{SD}	_	_	1.3	V	$V_{GS} = 0V, I_{S} = 13A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{ISS}	1	2,592	_		V _{DS} = 50V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	792	_	pF		
Reverse Transfer Capacitance	C _{RSS}	_	45	_			
Gate Resistance	R_g	_	2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_G	_	53.7	_			
Gate-Source Charge	Q _{GS}	_	10.6	_	nC	$V_{DD} = 50V, I_D = 13A,$	
Gate-Drain Charge	Q_{GD}	_	8.2	_		$V_{GS} = 10V$	
Turn-On Delay Time	t _{D(ON)}	_	11.6	_			
Turn-On Rise Time	t _R	_	14.1	_		$V_{DD} = 50V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	42.9	_	ns	$I_D = 13A$, $R_g = 6\Omega$	
Turn-Off Fall Time	t _F	_	22	_			
Reverse Recovery Time	t _{RR}	_	49.8	_	ns		
Reverse Recovery Charge	Q_{RR}	_	85.1	_	nC	I _F =13A, di/dt=100A/μs	

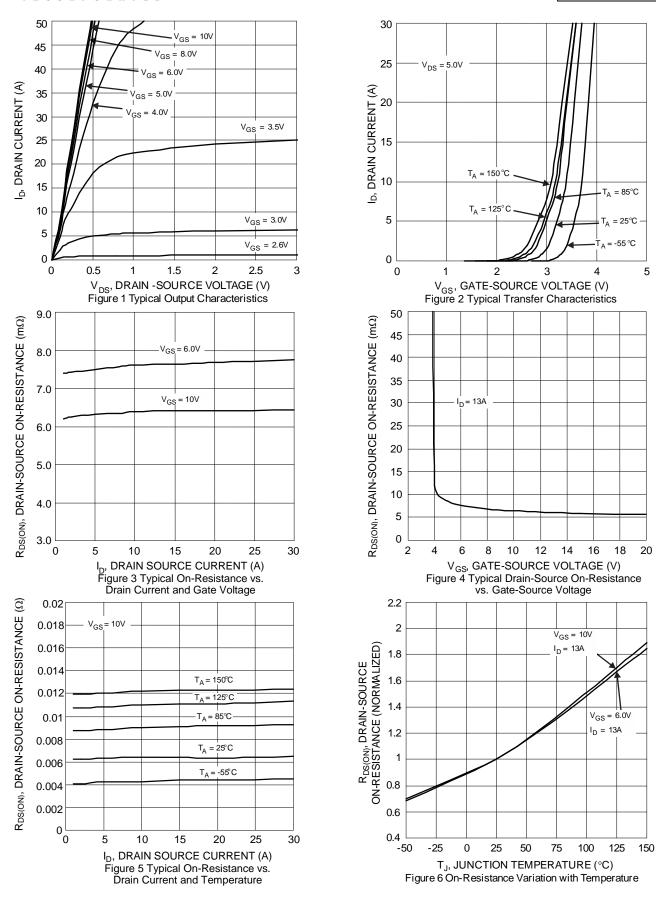
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{6.} Device mounted on infinite heat sink.

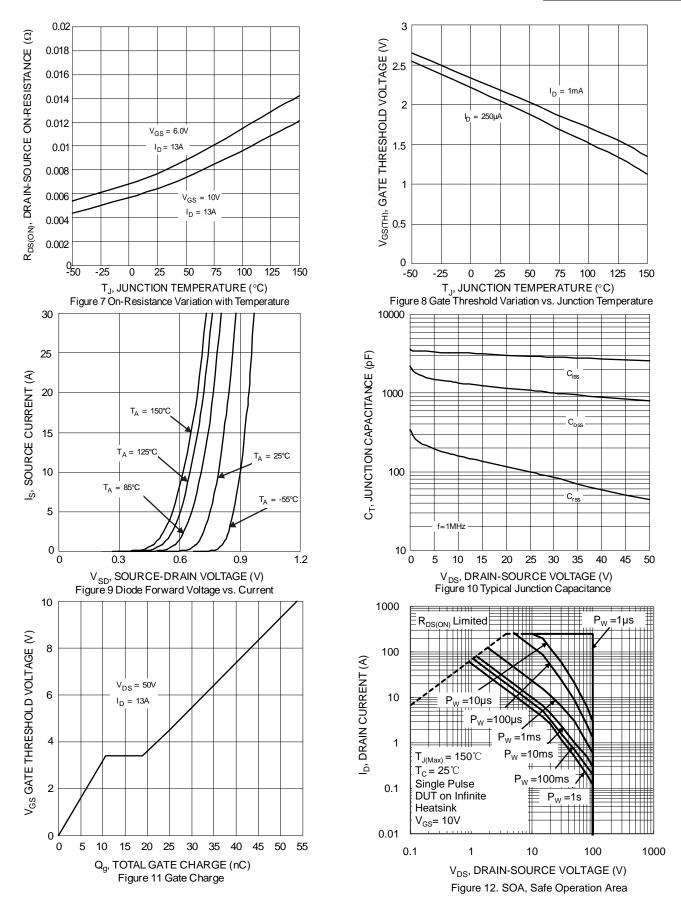
^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.

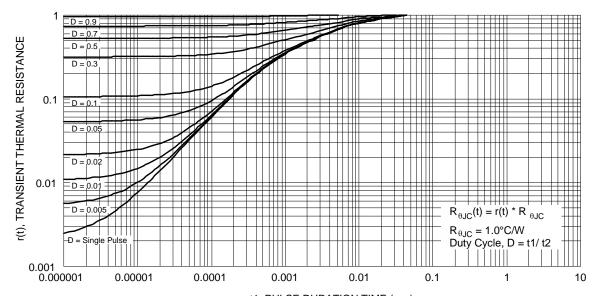










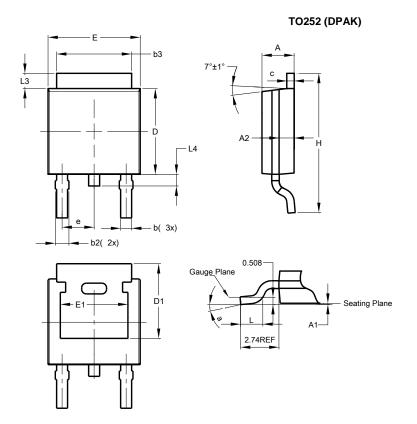


t1, PULSE DURATION TIME (sec) Figure 13 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

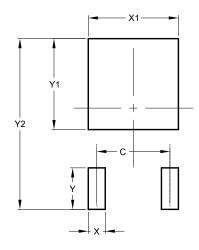


TO252 (DPAK)					
			Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
X	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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